

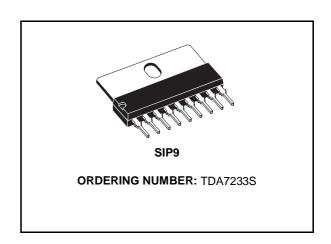


1W AUDIO AMPLIFIER WITH MUTE

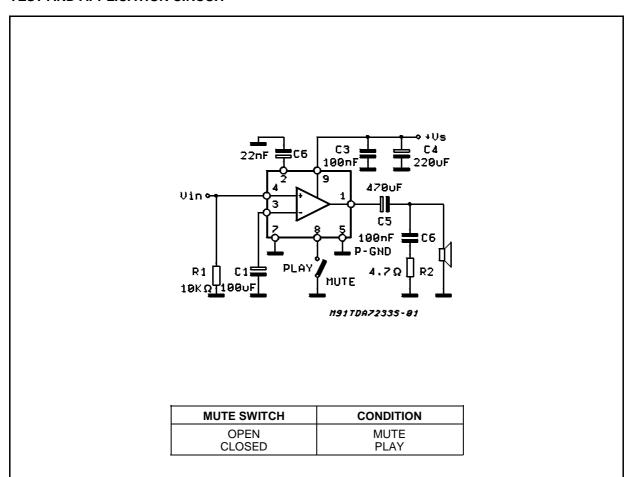
- OPERATING VOLTAGE 1.8 TO 15V
- EXTERNAL MUTE OR POWER DOWN FUNCTION
- IMPROVED SUPPLY VOLTAGE REJECTION
- LOW QUIESCENT CURRENT
- HIGH POWER CAPABILITY
- LOW CROSSOVER DISTORTION

DESCRIPTION

The TDA7233S is a monolithic integrated circuit in SIP 9, intended for use as class AB power amplifier with a wide range of supply voltage from 1.8V to 15V in portable radios, cassette recorders and players.

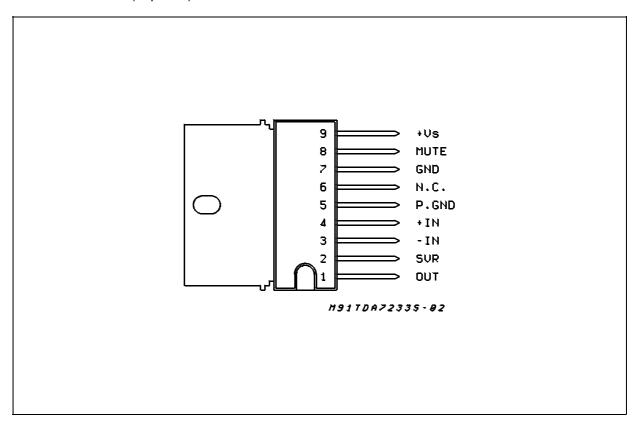


TEST AND APPLICATION CIRCUIT



May 1997 1/6

PIN CONNECTION (Top view)



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vs	Supply Voltage	16	V
Io	Output Peak Current	1	Α
P _{tot}	Total Power Dissipation T _{amb} = 50°C	1	W
T_{stg} , T_j	Storage and Junction Temperature	-40 to 150	°C

THERMAL DATA

Symbol	Description		Value	Unit
R _{th j-amb}	Thermal Resistance Junction-ambient	Max	70	°C/W
R _{th j-case}	Thermal Resistance Junction-pins	Max	10	°C/W



ELECTRICAL CHARACTERISTICS (V_S = 6V, T_{amb} = 25°C, unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Unit
Vs	Supply Voltage		1.8		15	V
Vo	Quiescent Output Voltage			27		V
		V _S = 3V V _S = 9V		1.2 4.2		V V
I _d	Quiescent Drain Current	PLAY		3.6	9	mA
		MUTE		0.4		mA
I _b	Input Bias Current			100		nA
Po	Output Power	$\begin{array}{lll} d = 10\% & f = 1 kHz \\ V_S = 12V & R_L = 8\Omega \\ V_S = 9V & R_L = 4\Omega \\ V_S = 9V & R_L = 8\Omega \\ V_S = 6V & R_L = 8\Omega \\ V_S = 6V & R_L = 4\Omega \\ V_S = 3V & R_L = 4\Omega \\ V_S = 3V & R_L = 8\Omega \end{array}$	0.8 0.45	1.9 1.6 1 0.4 0.7 110 70		W W W W W mW
d	Distortion	$P_O = 0.5W$ $R_L = 8\Omega$ $f = 1KHz$ $V_S = 9V$		0.3		%
G_V	Closed Loop Voltage Gain	f = 1KHz		39		dB
R _{IN}	Input Resistance	f = 1KHz	100			ΚΩ
e _N	Total Input Noise ($R_S = 10K\Omega$)	B = Curve A		2		μV
		B = 22Hz to 22KHz		3		μV
SVR	Supply Voltage Rejection	$R_g = 10K\Omega$ f = 100Hz	40	45		dB
	MUTE Attenuation	$V_0 = 1V$, $f = 100Hz$ to $10KHz$		70		dB
	MUTE Threshold			0.6		V
I _M	MUTE Current	V _S = 15V		0.4	2	mA

Figure 1: Output Power vs. Supply Voltage

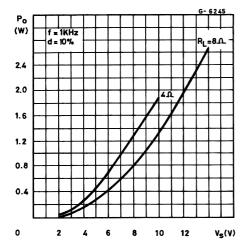


Figure 2: Supply Voltage Rejection vs. Frequency

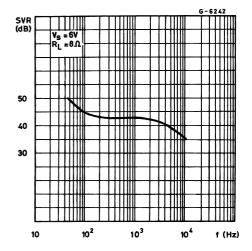


Figure 3: DC Output Voltage vs. Supply Voltage

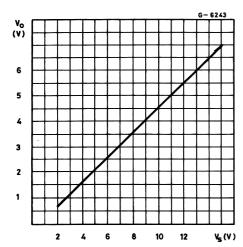


Figure 4: Quiescent Current vs. Supply Voltage

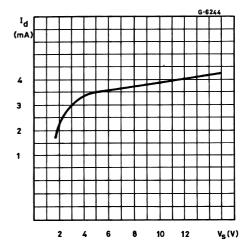
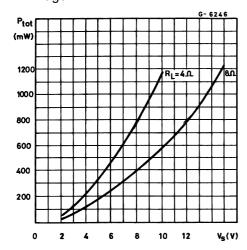
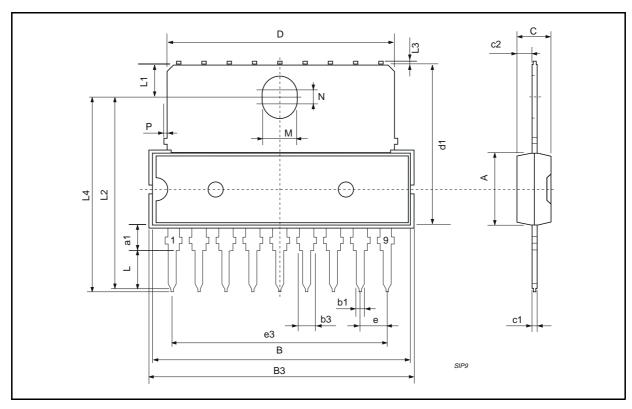


Figure 5: Total Dissipated Power vs. Supply Voltage



SIP9 PACKAGE MECHANICAL DATA

DIM.		mm			inch	
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
Α			7.1			0.280
a1	2.7		3	0.106		0.118
В			23			0.90
B3			24.8			0.976
b1		0.5			0.020	
b3	0.85		1.6	0.033		0.063
С		3.3			0.130	
c1		0.43			0.017	
c2		1.32			0.052	
D			21.2			0.835
d1		14.5			0.571	
е		2.54			0.100	
e3		20.32			0.800	
L	3.1			0.122		
L1		3			0.118	
L2		17.6			0.693	
L3			0.25			0.010
L4	17.4		17.85	0.685		0,702
М		3.2			0.126	
N		1			0.039	
Р			0.15			0.006



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